

**Amendments to the Claims:**

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A method for producing an SOI wafer by the hydrogen ion delamination method comprising at least a step of bonding a base wafer and a bond wafer having a micro bubble layer formed by gas ion implantation and a step of delaminating a wafer having an SOI layer at the micro bubble layer as a border, wherein a CZ wafer produced from a single crystal ingot of which COPs are reduced for the whole crystal is used as the bond ~~wafer-wafer~~, and wherein the wafer having an SOI layer is subjected to a heat treatment under an atmosphere containing hydrogen or argon in a batch processing type furnace after the delamination step.
2. (Canceled)
3. (Currently Amended) An SOI wafer produced by the method according to ~~Claim 2, which~~ Claim 1, wherein the SOI wafer has an RMS value of 0.5 nm or less concerning surface roughness for both of 1  $\mu\text{m}$  square and 10  $\mu\text{m}$  square.